

Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D
85V	11mΩ@10V	50A
	15mΩ@4.5V	

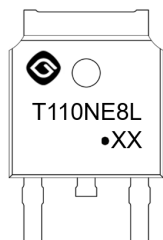
Feature

- Split Gate Trench Technology
- Low R_{DS(ON)}
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

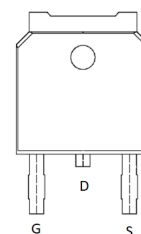
- Power Switching Application

MARKING:

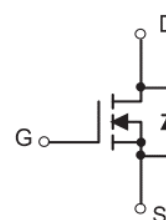


T110NE8L = Device Code
XX = Date Code
Solid Dot = Green Indicator

TO-252-2L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V _{DS}	85	V
Gate - Source Voltage		V _{GS}	±20	V
Continuous Drain Current ¹	T _C = 25°C	I _D	50	A
	T _C = 100°C	I _D	32	A
Pulsed Drain Current ²		I _{DM}	200	A
Single Pulsed Avalanche Current ³		I _{AS}	22	A
Single Pulsed Avalanche Energy ³		E _{AS}	117	mJ
Power Dissipation ⁵	T _C = 25°C	P _D	72.5	W
Thermal Resistance from Junction to Ambient ⁶		R _{θJA}	52	°C/W
Thermal Resistance from Junction to Case		R _{θJC}	2	°C/W
Junction Temperature		T _J	150	°C
Storage Temperature		T _{STG}	-55~ +150	°C

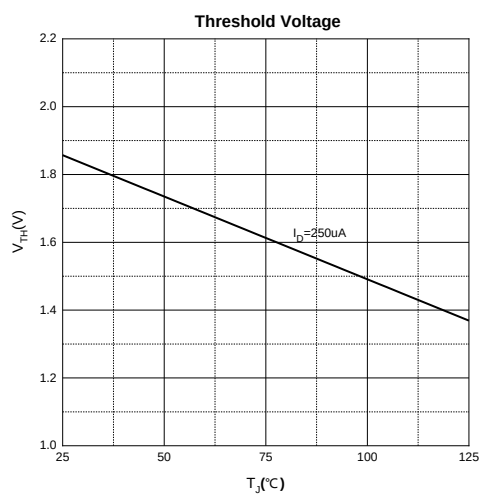
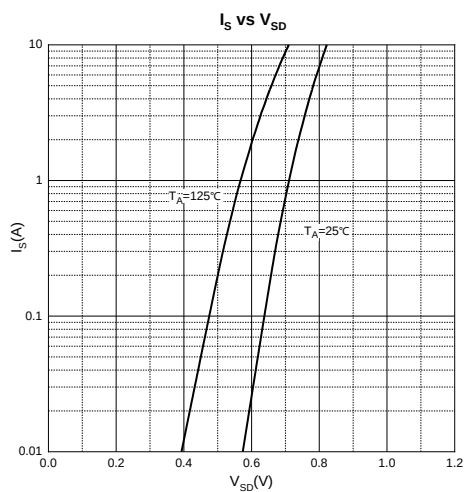
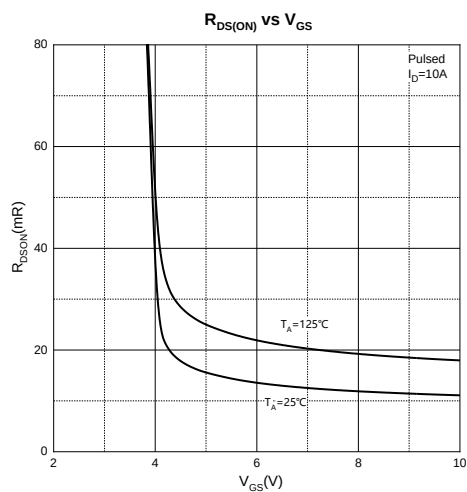
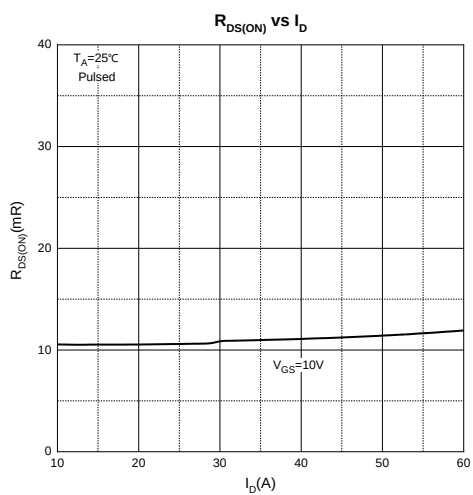
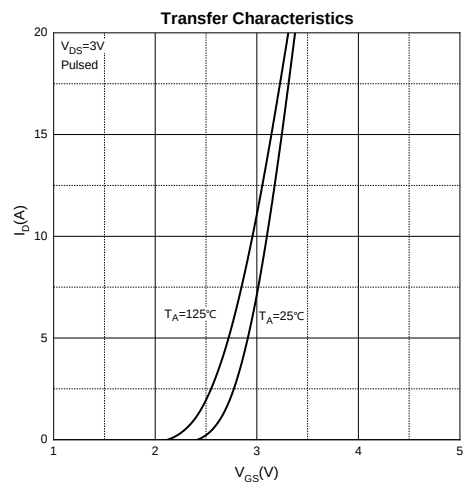
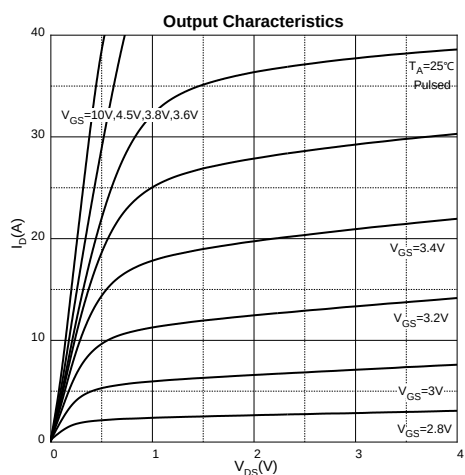
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

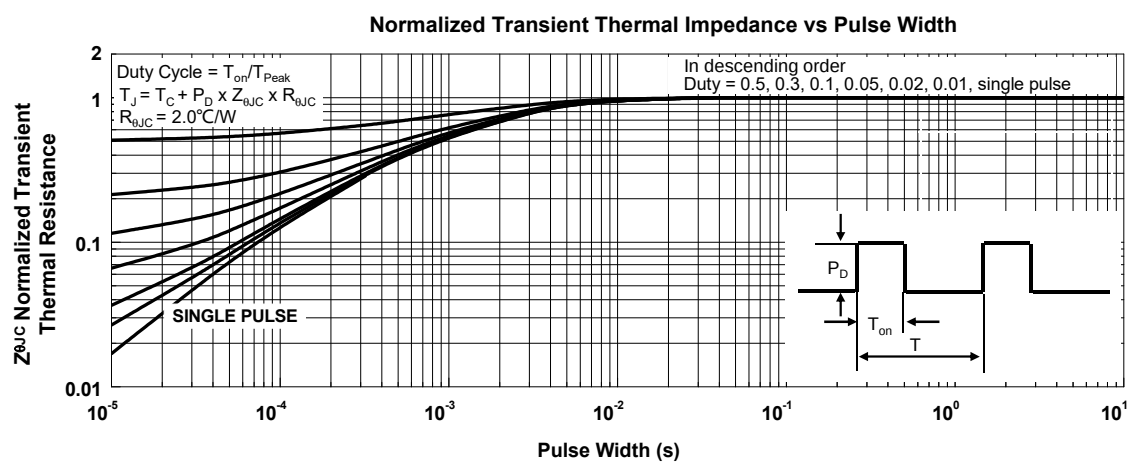
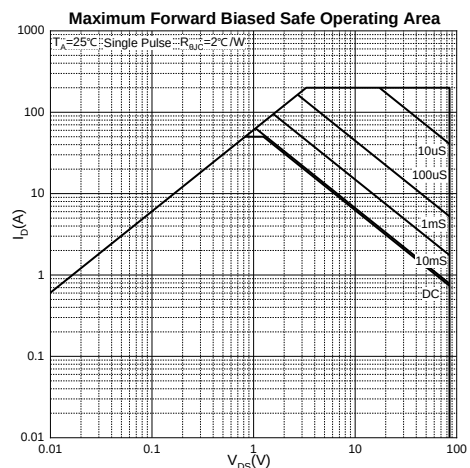
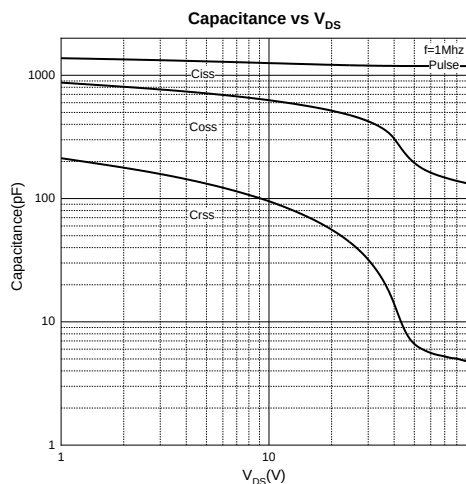
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	85			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 68V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	1.8	2.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		11	15	m Ω
		$V_{GS} = 4.5V, I_D = 10A$		15	19	
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 20A$	10			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 45V, V_{GS} = 0V, f = 1MHz$		1196		pF
Output Capacitance	C_{oss}			250		
Reverse Transfer Capacitance	C_{rss}			11		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DD} = 40V, V_{GS} = 10V, I_D = 20A$		23		nC
Gate-source Charge	Q_{gs}			4		
Gate-drain Charge	Q_{gd}			6.2		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 40V, V_{GS} = 10V, I_D = 50A$ $R_G = 6\Omega$		12		ns
Turn-on Rise Time	t_r			13		
Turn-off Delay Ttime	$t_{d(off)}$			16		
Turn-off Fall Time	t_f			5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$		0.9	1.2	V

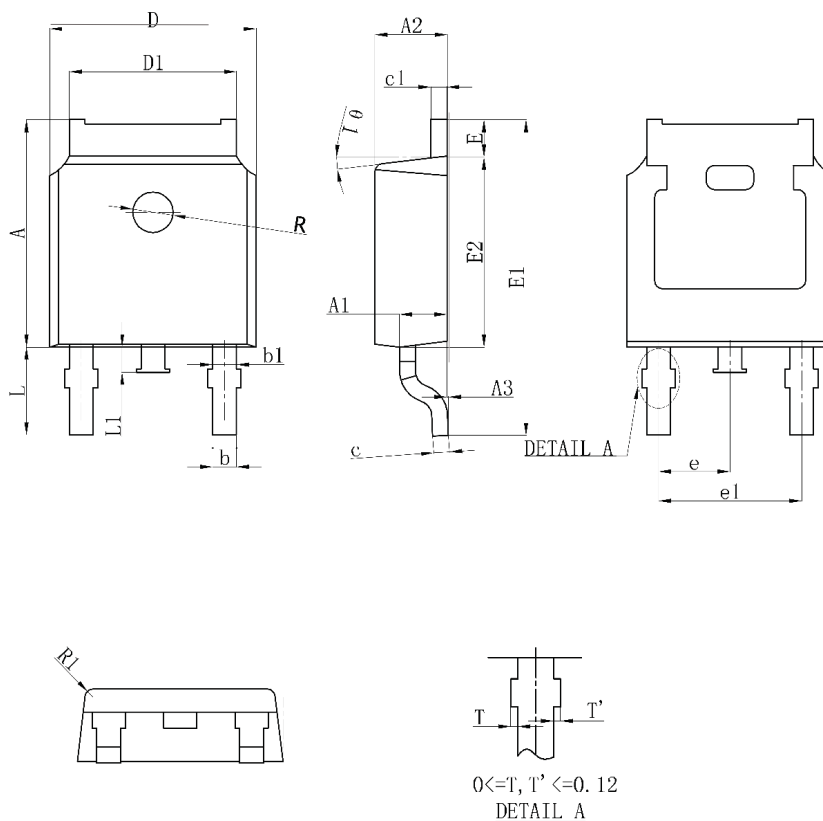
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 40V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^{\circ}\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^{\circ}\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$.

Typical Characteristics





TO-252-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	7.050	7.150	0.278	0.281
A1	0.960	1.060	0.038	0.042
A2	2.200	2.400	0.087	0.094
A3	0.000	0.100	0.000	0.004
b	0.760REF		0.030REF	
b1	1.000REF		0.039REF	
c	0.508REF		0.020REF	
c1	0.508REF		0.020REF	
D	6.550	6.650	0.258	0.262
D1	5.100	5.460	0.201	0.215
E	0.950	1.050	0.037	0.041
E1	9.700	10.400	0.382	0.409
E2	6.000	6.200	0.236	0.244
e	2.286BSC		0.090BSC	
e1	4.572REF		0.180REF	
L	2.650	2.950	0.104	0.116
L1	0.700	0.900	0.028	0.035
θ1	7°REF		7°REF	
R	1.300REF		0.051REF	
R1	0.250REF		0.010REF	